



Technical Data Sheet

Infrared LED

ZIRP08C



Descriptions

The ZIRP08C is a high intensity diode, molded in a water clear plastic package. The miniature side-facing device has a chip, that emits radiation from the side of the clear package.

Features

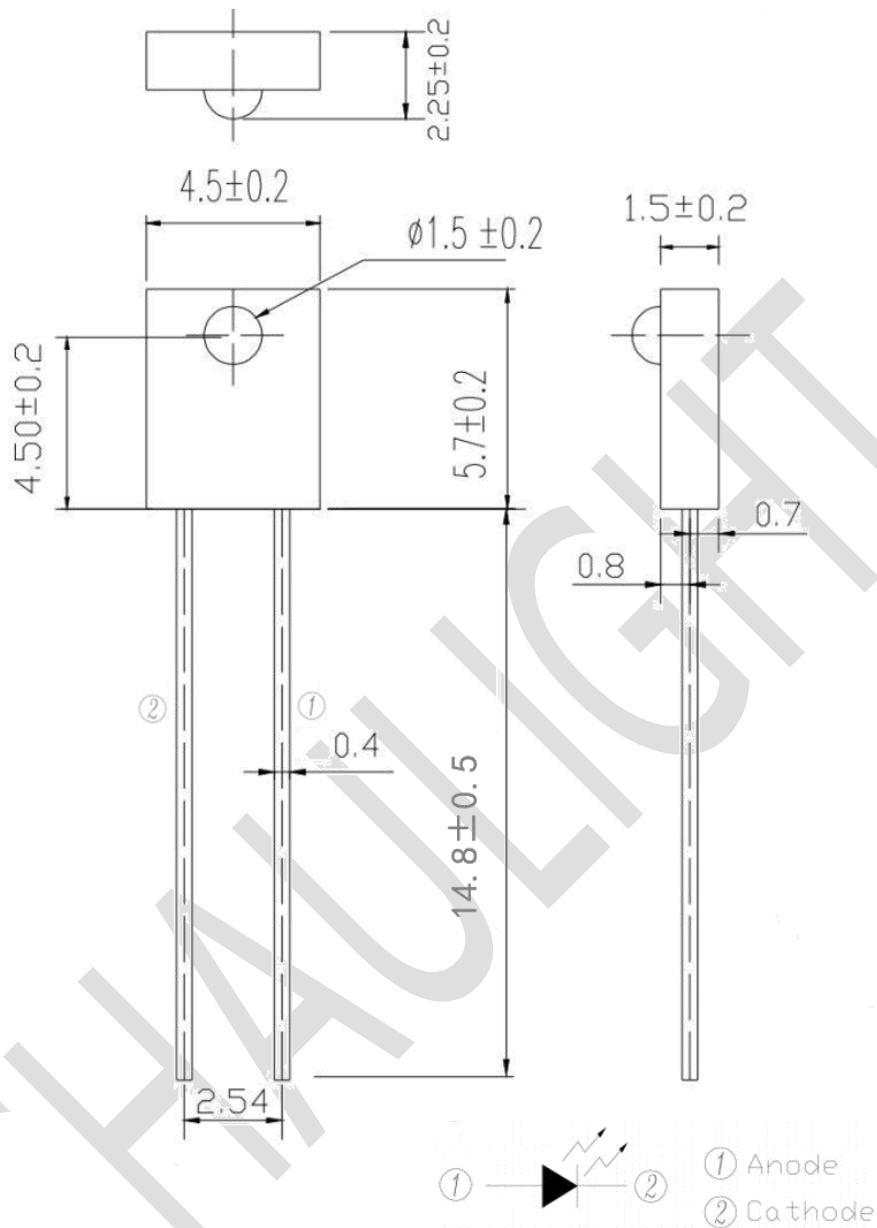
- High reliability
- High radiant intensity
- Peak wavelength $\lambda_p=940\text{nm}$
- Low forward voltage
- Pb.Free
- This product itself will remain within RoHS compliant version.

Applications

- Mouse
- Optoelectronic switch
- Copiers
- Scanners
- Amusement machines



Package Dimension



Notes:

1. All dimensions are in millimeters
2. Tolerances unless dimensions ± 0.3 mm
3. Lead spacing is measured where the lead emerge from the package



Absolute Maximum Ratings

Parameter (Ta=25°C)	Symbol	Ratings	Unit
Power Dissipation at(or below)25°C cfree Air Temperature	Pd	75	mW
Reverse Voltage	V _R	5	V
Forward Current	I _F	50	mA
Peak Forward Current Pulse width ≤ 100μs,Duty cycle= 1%	I _{FP}	1	A
Operating Temperature	T _{opr}	-40~+100	°C
Storage Temperature	T _{stg}	-40~+100	°C
Lead Soldering Temperature (2mm form body for 5 seconds)	T _{sol}	260	°C

Electro-Optical Characteristics

Paramete (Ta=25°C)	Symbol	Condition	Min.	Typ.	Max.	Units
Light Current	I _{c(ON)}	I _F =4mA,V _{CE} =3.5V	490	--	710	μA
Peak Wavelength	λ _p	I _F =20mA	--	940	--	nm
Spectral Bandwidth	Δλ	I _F =20mA	--	45	--	nm
Forward Voltage	V _F	I _F =20mA	--	1.2	1.5	V
Reverse Current	I _R	V _R =5V	--	--	10	μA
View Angle	2θ1/2	I _F =20mA	--	60	--	deg



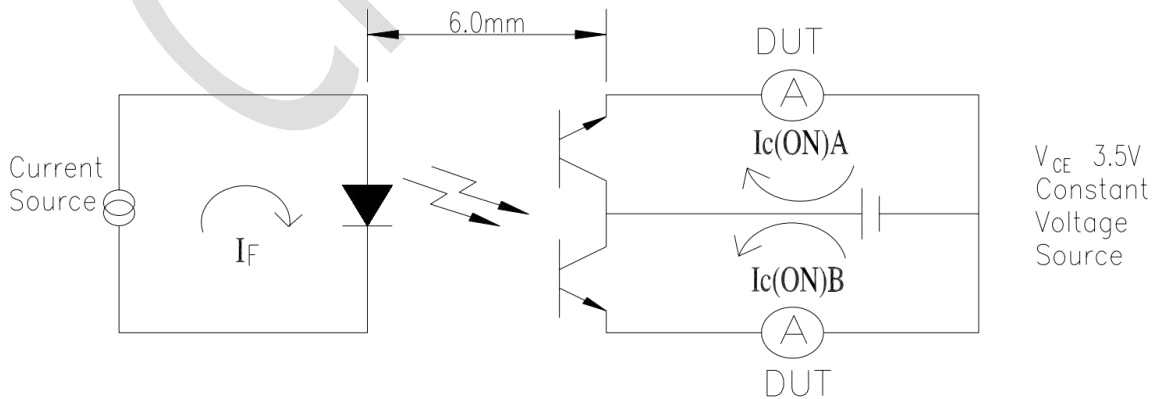
Rank

Parameter	Symbol	Condition	Min.	Max.	Unit
E6	I _{c(ON)}	I _F =4mA, V _{CE} =3.5V	490	710	μA

Test Method For I_{c(ON)}:

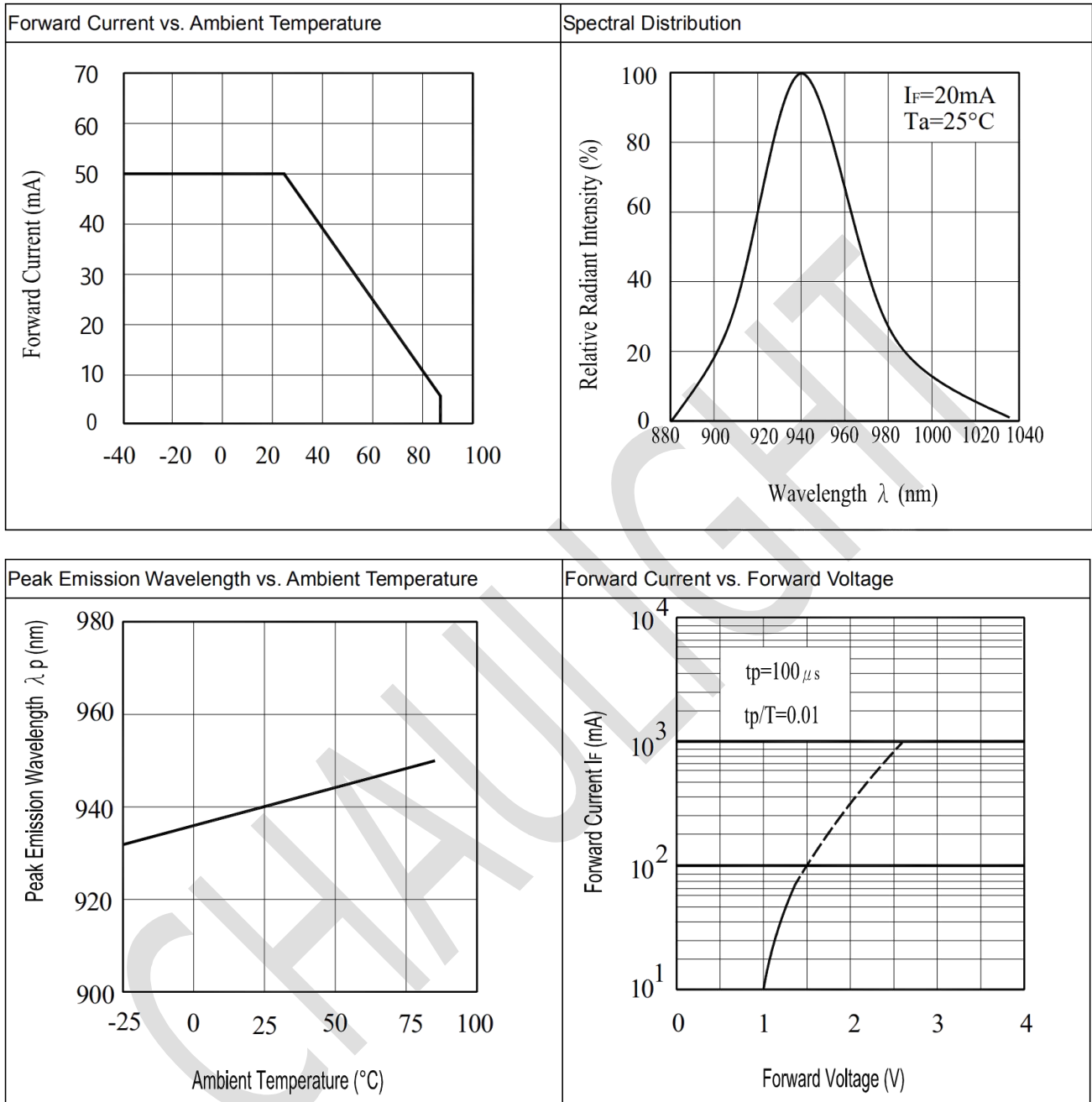
Condition: I_F=4mA, V_{CE}=3.5V

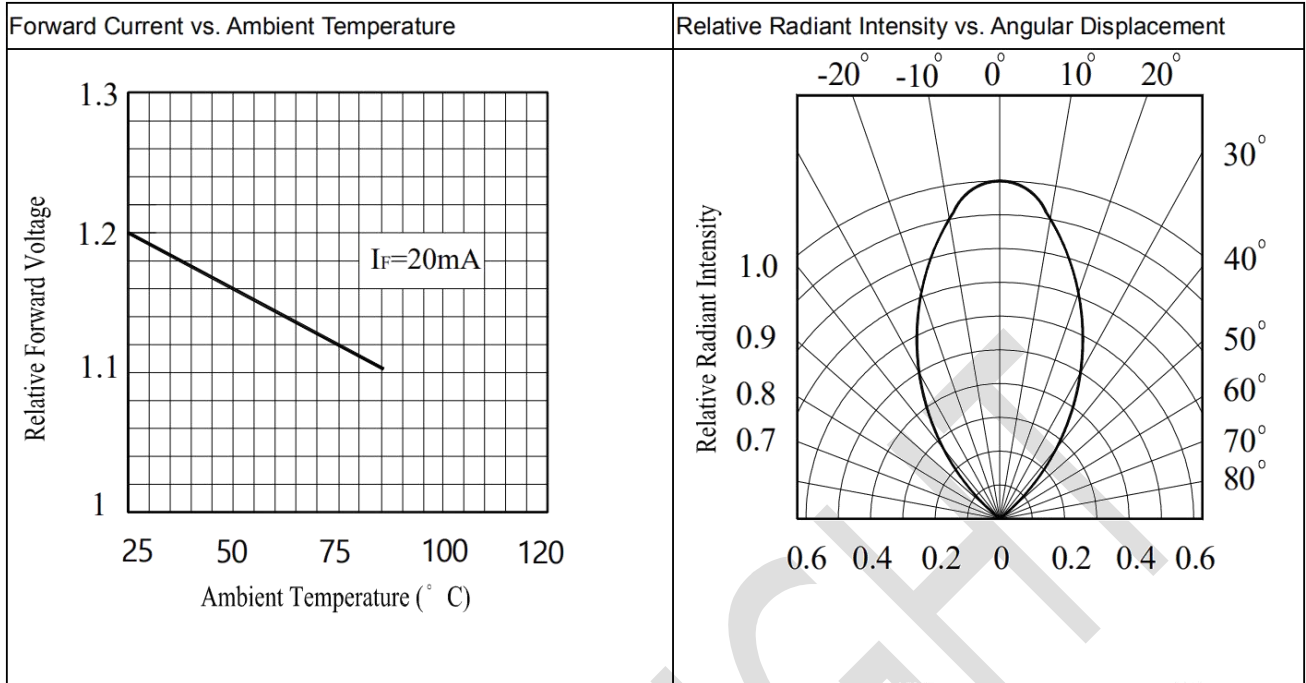
The intensity testing method for infrared emitting diode





Typical Electrical/Optical/Characteristics Curves





Packing Quantity Specification

1. 1000PCS/1Bag, 8Bags/1Box
2. 10Boxes/1Carton